

GSB1132

PNP EPITAXIAL SILICON TRANSISTOR

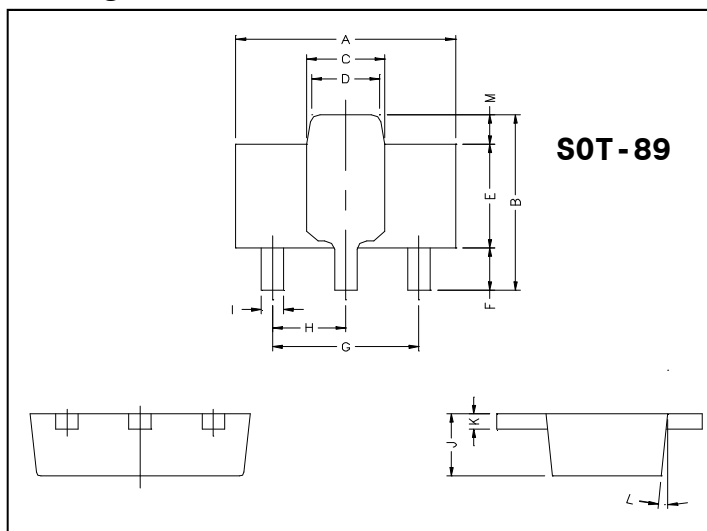
Description

The GSB1132 is a epitaxial planar type PNP silicon transistor .

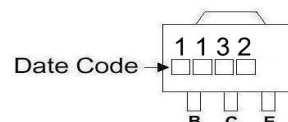
Features

Low $V_{CE(sat)}$. $V_{CE(sat)} = -0.2V(Typ.)$ ($I_C/I_B = -500mA / -50 mA$)

Package Dimensions



Marking :



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	4.4	4.6	G	3.00	REF.
B	4.05	4.25	H	1.50	REF.
C	1.50	1.70	I	0.40	0.52
D	1.30	1.50	J	1.40	1.60
E	2.40	2.60	K	0.35	0.41
F	0.89	1.20	L	5°	TYP.
			M	0.70	REF.

Absolute Maximum Ratings (Ta = 25°C, unless otherwise specified)

Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	°C
Storage Temperature	Tstg	-55 ~ +150	°C
Collector to Base Voltage	Vcbo	-40	V
Collector to Emitter Voltage	Vceo	-32	V
Emitter to Base Voltage	Vebo	-5	V
Collector Current(DC)	Ic	-1	A
Collector Current(PULSE) (note1)	Ic	-2	A
Collector Power Dissipation	Pd	0.5	W
Collector Power Dissipation (note2)	Pd	2	W

Note 1: Single pulse, PW=100ms

Note 2: When mounted on a 40*40*0.7 mm ceramic board.

Electrical Characteristics (Ta = 25°C, unless otherwise specified)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVcbo	-40	-	-	V	IC=-50uA
BVceo	-32	-	-	V	IC=-1mA
BVebo	-5	-	-	V	IE=-50uA
Icbo	-	-	-0.5	uA	VCB=-20V
IEBO	-	-	-0.5	uA	VEB=-4V
VCE(sat)	-	-0.2	-0.5	V	IC=-500mA, IB=-50mA(note)
hFE	82	-	390		VCE=-3V, IC=-100mA
fT	-	150	-	MHz	VCE=-5V, IE=-50mA, f=30MHz
Cob	-	20	30	pF	VCE=-10V, IE=0A, f=1MHz

Note: Measured using pulse current.

Classification Of hFE

Rank	P	Q	R
RANGE	82 - 180	120 - 270	180 - 390

Characteristics Curve

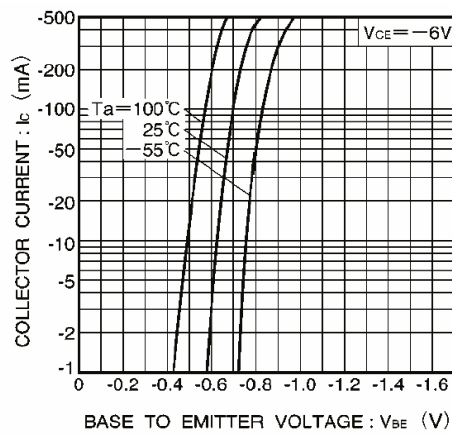


Fig.1 Grounded emitter propagation characteristics

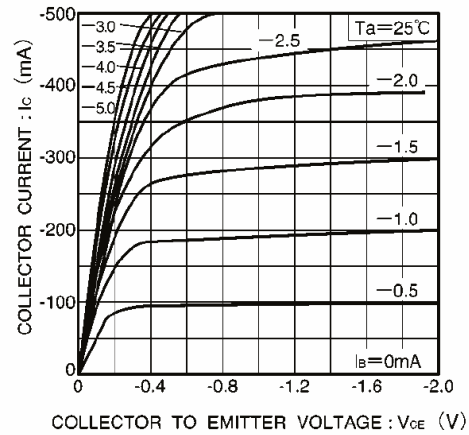


Fig.2 Grounded emitter output characteristics

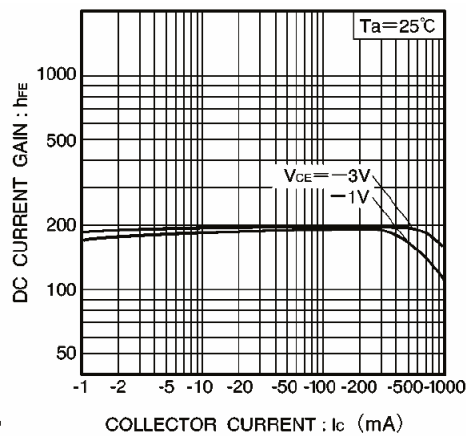


Fig.3 DC current gain vs. collector current (I)

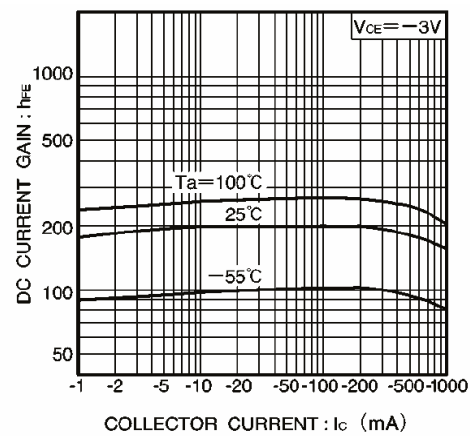


Fig.4 DC current gain vs. collector current (II)

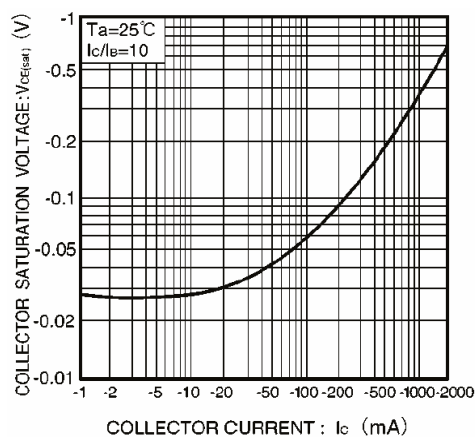


Fig.5 Collector-emitter saturation voltage vs. collector current

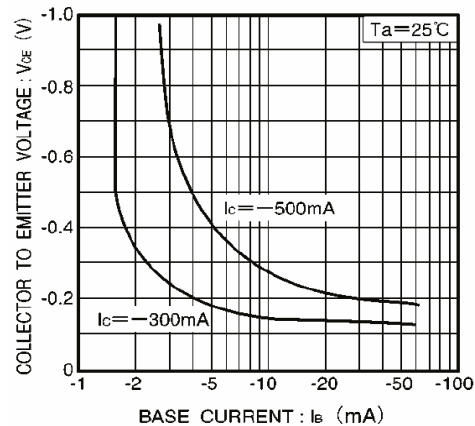
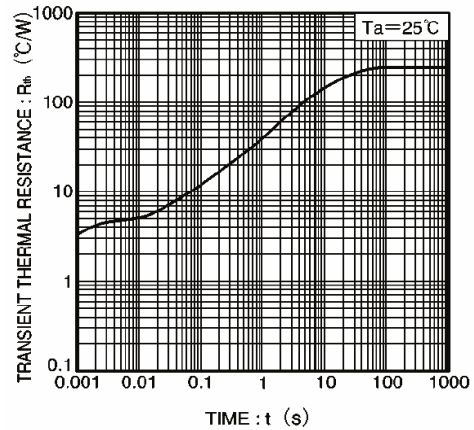
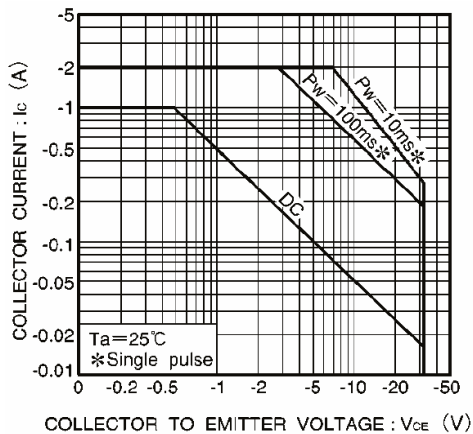
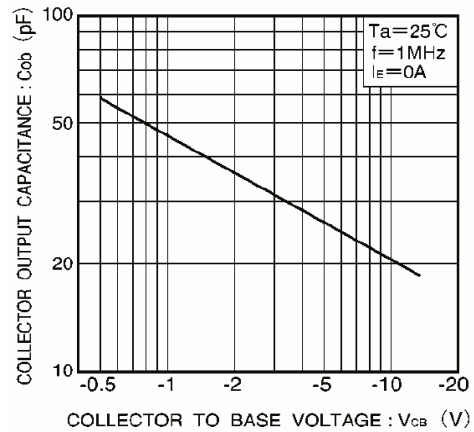
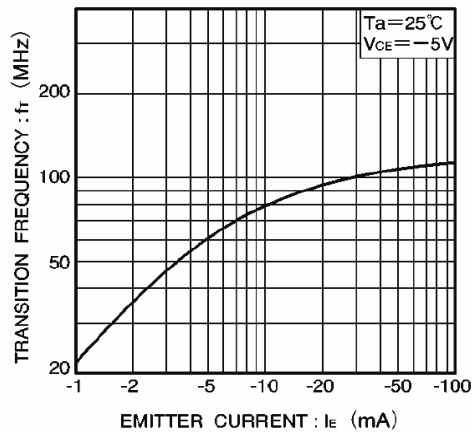


Fig.6 Collector-emitter saturation voltage vs. base current



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